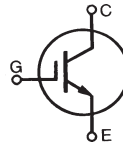


GenX3™ 600V IGBT

IXGA48N60B3
IXGP48N60B3
IXGH48N60B3

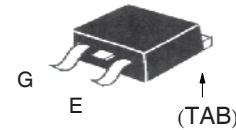
Medium speed low V_{sat} PT
 IGBTs 5-40 kHz switching



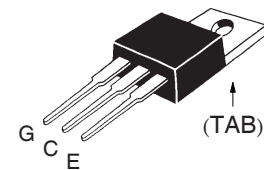
V_{CES} = 600V
I_{C110} = 48A
V_{CE(sat)} ≤ 1.8V

Symbol	Test Conditions	Maximum Ratings	
V _{CES}	T _C = 25°C to 150°C	600	V
V _{CGR}	T _J = 25°C to 150°C, R _{GE} = 1MΩ	600	V
V _{GES}	Continuous	± 20	V
V _{GEM}	Transient	± 30	V
I _{C110}	T _C = 110°C	48	A
I _{CM}	T _C = 25°C, 1ms	280	A
SSOA (RBSOA)	V _{GE} = 15V, T _{VJ} = 125°C, R _G = 5Ω Clamped inductive load @ ≤ 600V	I _{CM} = 120	A
P _C	T _C = 25°C	300	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6mm (0.062 in.) from case for 10s	300	°C
T _{SOLD}	Plastic body for 10 seconds	260	°C
M _d	Mounting torque (TO-247)(TO-220)	1.13/10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

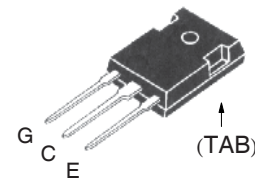
TO-263 (IXGA)



TO-220 (IXGP)



TO-247 (IXGH)



G = Gate C = Collector
 E = Emitter TAB = Collector

Features

- Optimized for low conduction and switching losses
- Square RBSOA
- International standard packages

Advantages

- High power density
- Low gate drive requirement

Applications

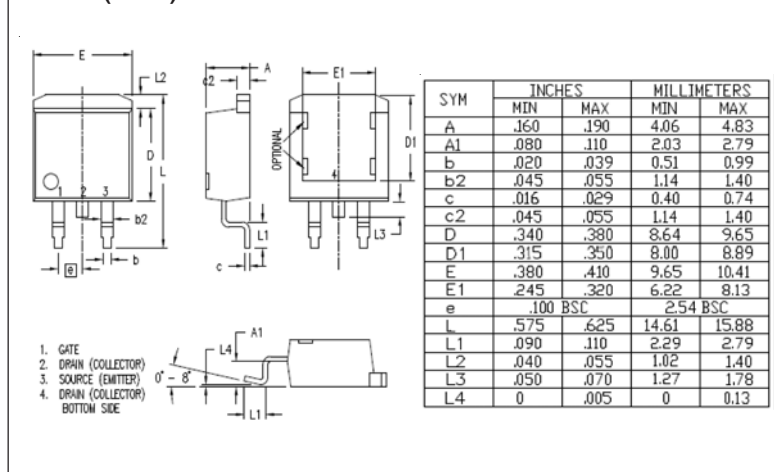
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV _{CES}	I _C = 250μA, V _{GE} = 0V	600		V
V _{GE(th)}	I _C = 250μA, V _{CE} = V _{GE}	3.0		5.0 V
I _{CES}	V _{CE} = V _{CES}			25 μA
	V _{GE} = 0V T _J = 125°C			250 μA
I _{GES}	V _{CE} = 0V, V _{GE} = ± 20V			±100 nA
V _{CE(sat)}	I _C = 32A, V _{GE} = 15V, Note 1			1.8 V

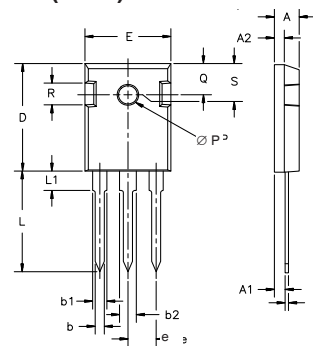
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 30A, V_{CE} = 10V, \text{Note 1}$	28	46	S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		3980	pF
C_{oes}			170	pF
C_{res}			45	pF
Q_g	$I_C = 40A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		115	nC
Q_{ge}			21	nC
Q_{gc}			40	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ C$ $I_C = 30A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 5\Omega$		22	ns
t_{ri}			25	ns
E_{on}			0.84	mJ
$t_{d(off)}$			130	200 ns
t_{fi}			116	200 ns
E_{off}			0.66	1.20 mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ C$ $I_C = 30A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 5\Omega$		19	ns
t_{ri}			25	ns
E_{on}			1.71	mJ
$t_{d(off)}$			190	ns
t_{fi}			157	ns
E_{off}			1.30	mJ
R_{thJC}			0.42	$^\circ C/W$
R_{thCS}	(TO-247)	0.25		$^\circ C/W$
	(TO-220)	0.50		$^\circ C/W$

Note 1: Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

TO-263 (IXGA) Outline

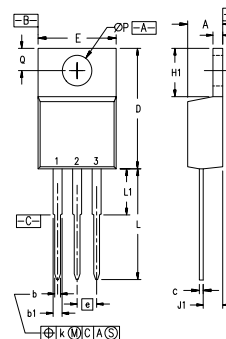


TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-220 (IXGP) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
∅P	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

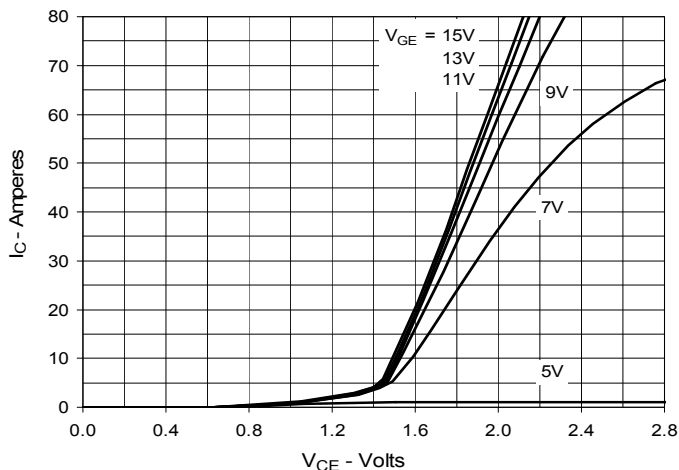


Fig. 2. Extended Output Characteristics @ 25°C

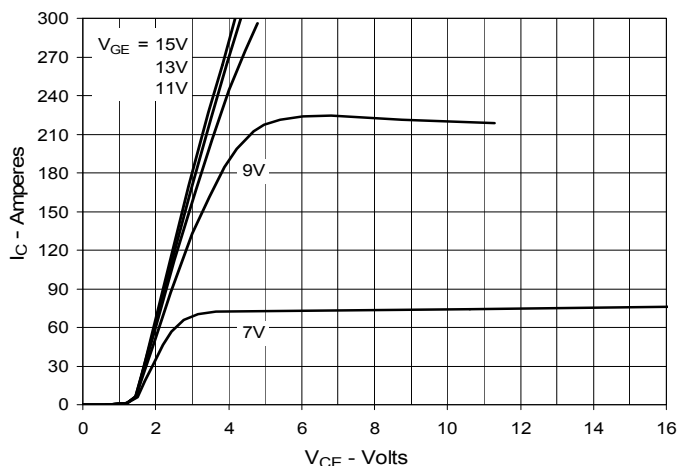


Fig. 3. Output Characteristics @ 125°C

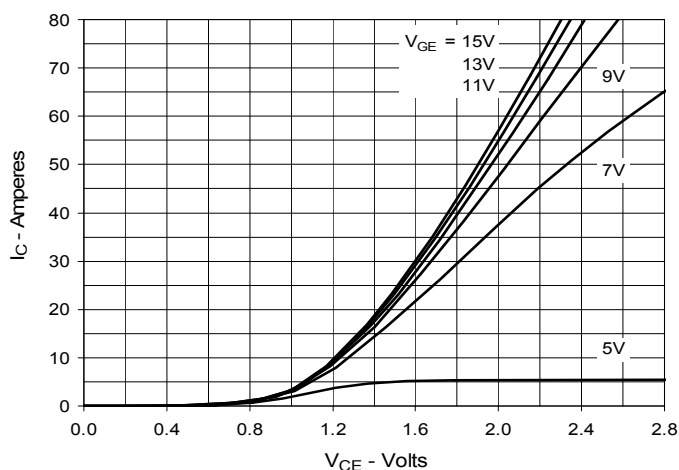


Fig. 4. Dependence of Vce(sat) on Junction Temperature

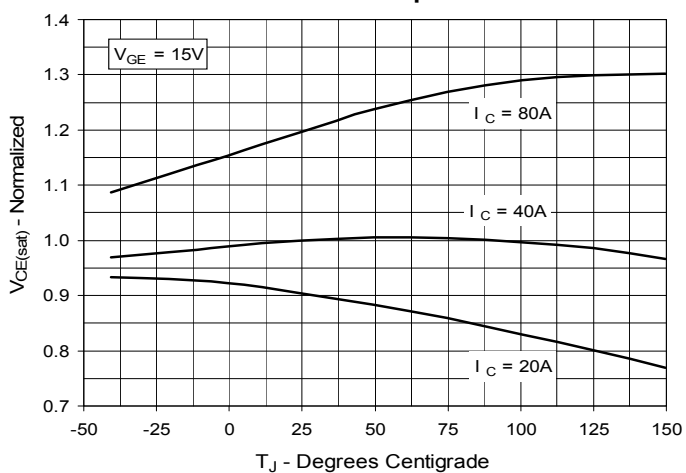


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

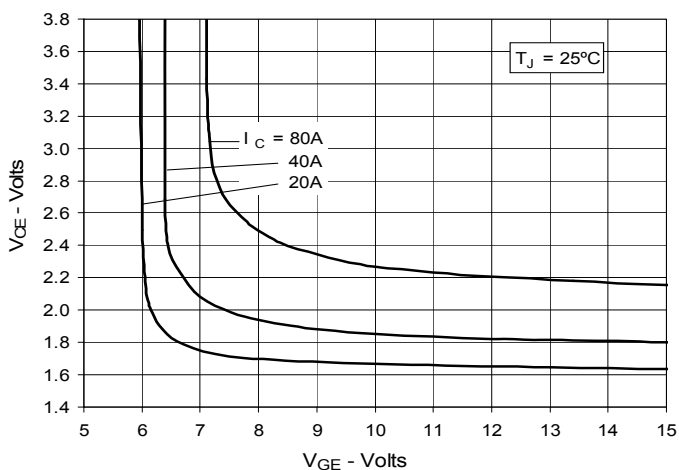


Fig. 6. Input Admittance

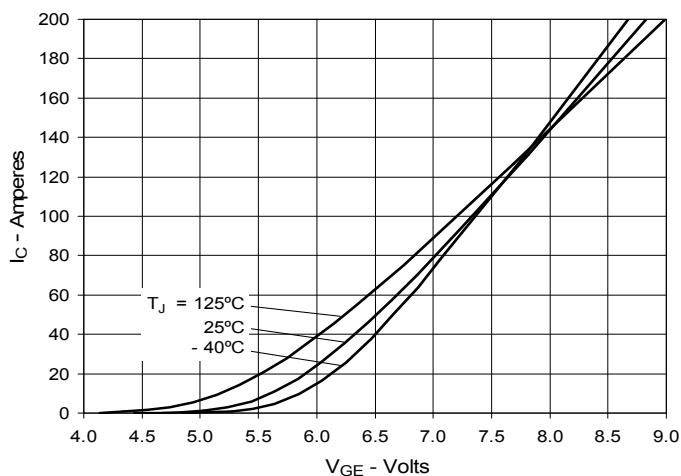


Fig. 7. Transconductance

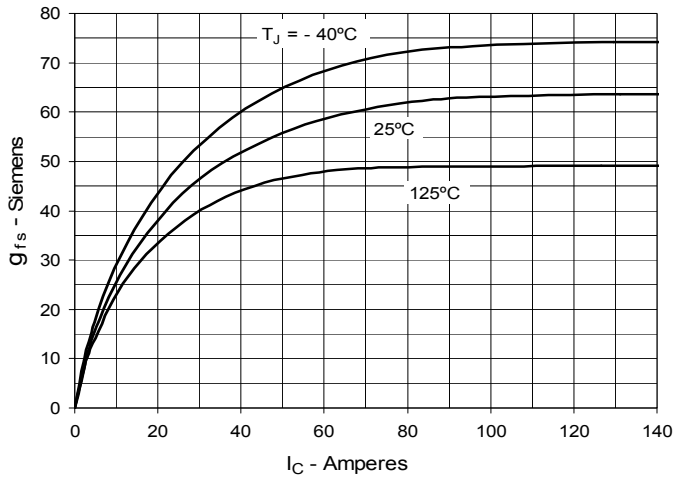


Fig. 8. Gate Charge

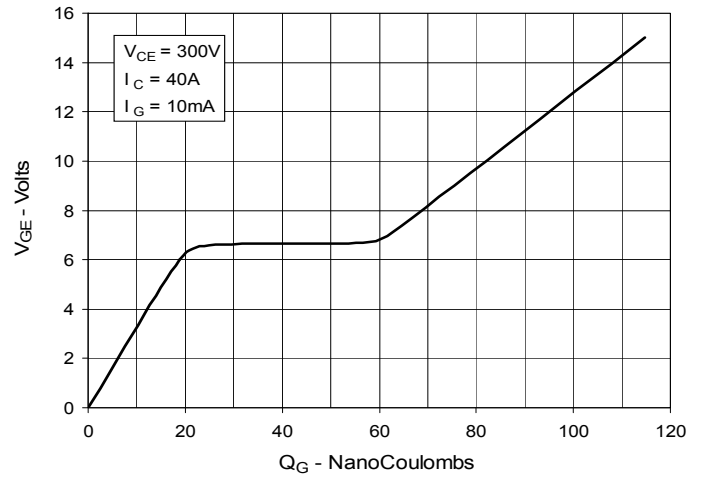


Fig. 9. Capacitance

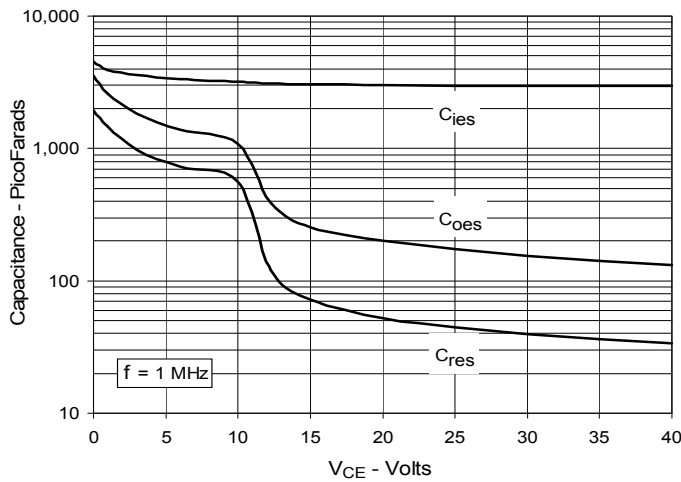


Fig. 10. Reverse-Bias Safe Operating Area

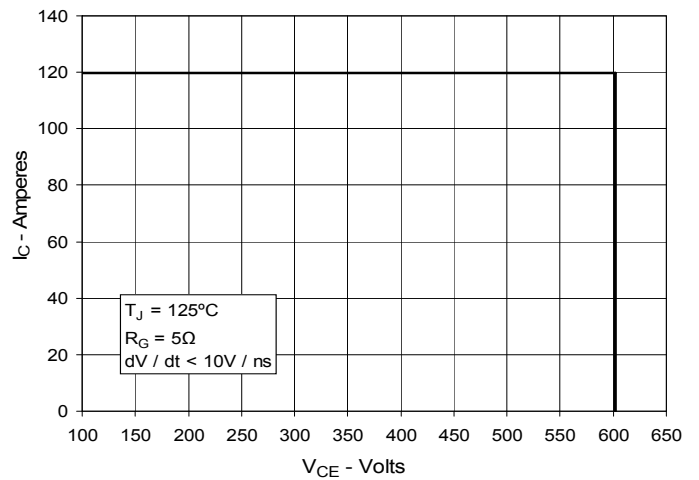
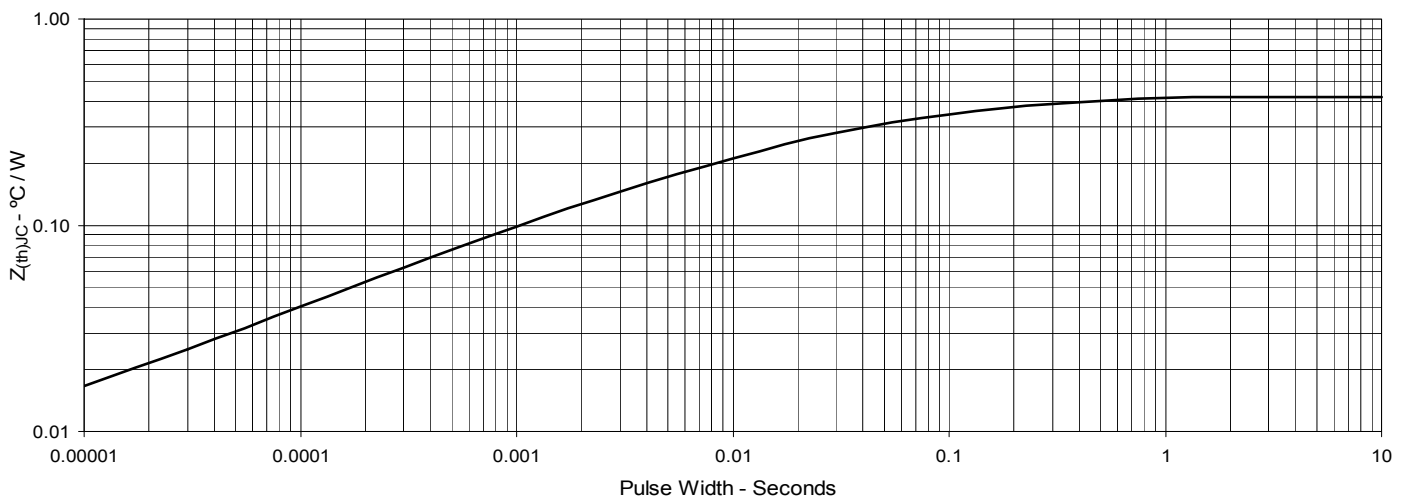


Fig. 11. Maximum Transient Thermal Impedance



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Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

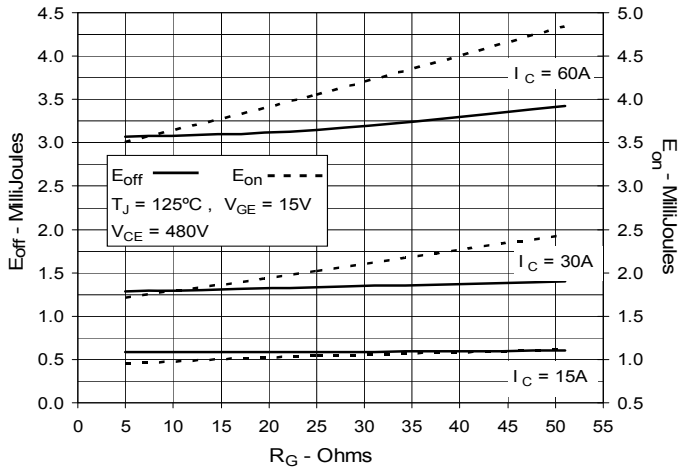


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

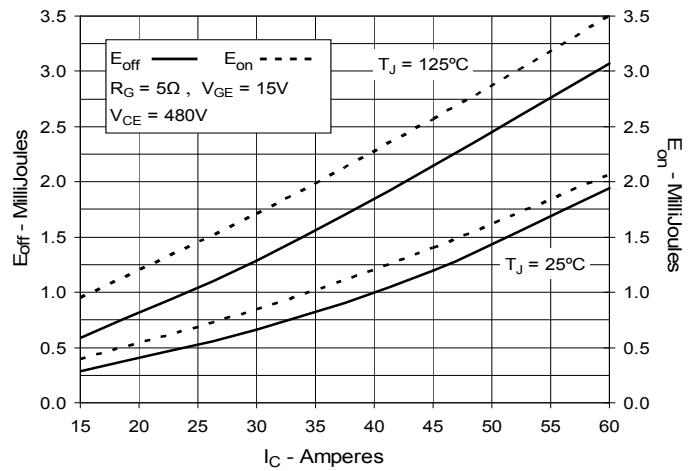


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

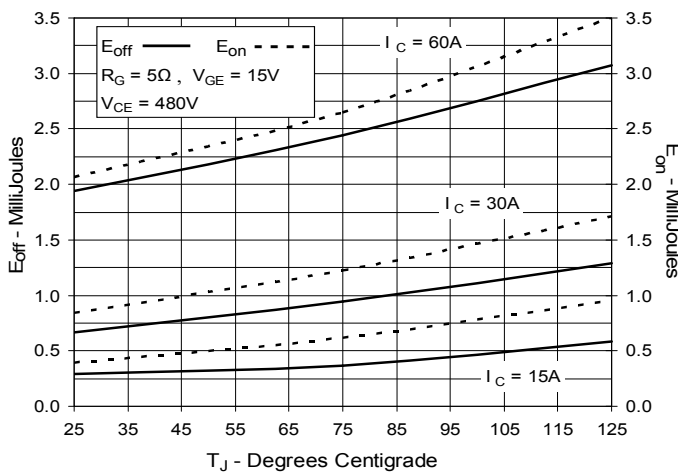


Fig. 15. Inductive Turn-off Switching Times vs. Junction Temperature

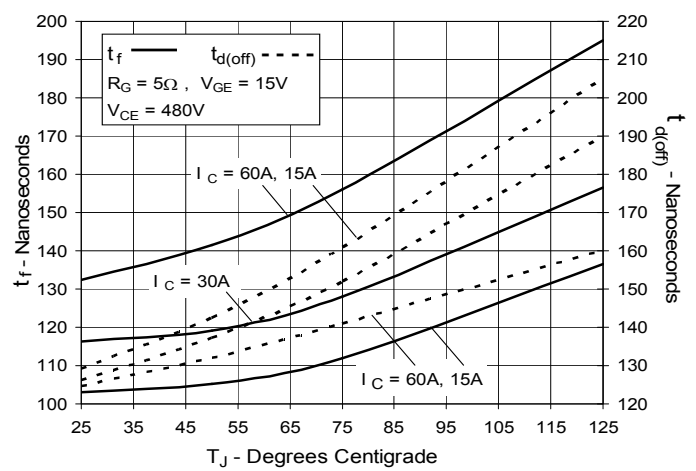


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

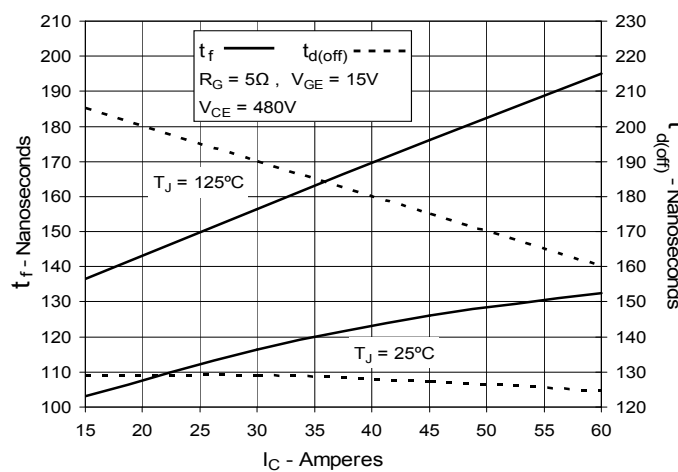
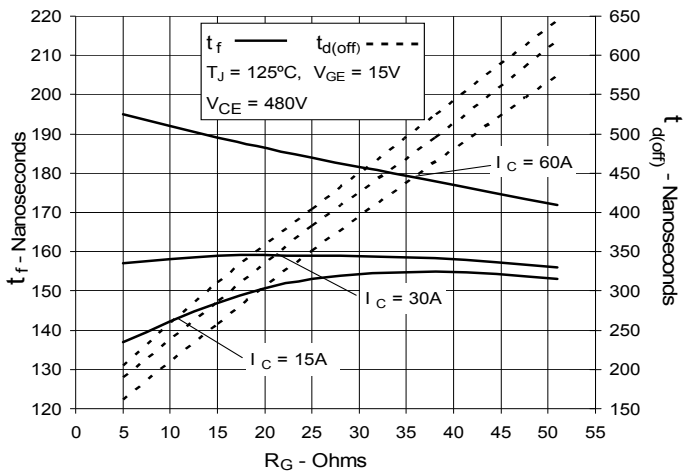
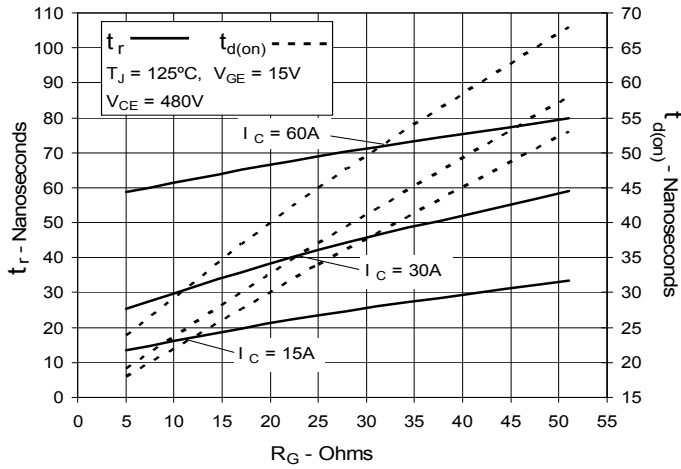


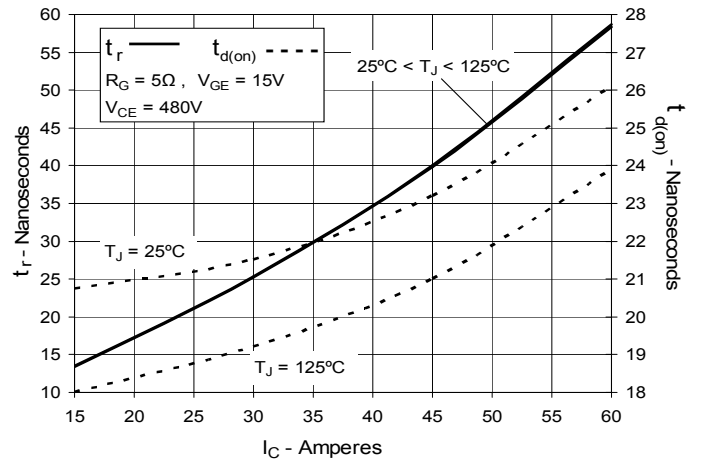
Fig. 17. Inductive Turn-off Switching Times vs. Gate Resistance



**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**

